Receipt date: 03/19/2009

INFORMATION DISCLOSURE CITATION			ATION DISCLOSURE	ATTY. DOCKET NO.		SE	SERIAL NO.			
			CITATION	925-327 APPLICANT		10	0/552,268			
(Use several sheets if necessary)				ASANO ET AL.			OUP			
				October 6, 2005 2814			14			
*EXAN	/INER				J.S. PATENT DOC	JMENTS			FILING	DATE
INIT			DOCUMENT NUMBER	DATE	N	AME	CLASS	SUBCLASS		
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DOCUMENT			DOCUMENT	DATE COUNTRY			TRANSLATION CLASS SUBCLASS YES NO			
			Восомент	DATE	300	5141141	02,100	00802,100	120	
					including Author,					
	/B.J / Xie et al, "A High-Current and High-Temperature 6H-SiC Thyristor", IEEE Electron Device Letters, vol. 17, no. 3, March 1996, pp. 142-144									
*Exar	niner		/Bilkis Jahan/		D	ate Considered	04/24/20	009		

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)